

Electronic Materials and Photonics

Room 114 - Session EM+2D+AP+QS+TF-ThM

Epitaxy: Advances in Materials Integration and Devices

Moderator: Somil Rathi, Arizona State University

8:00am **EM+2D+AP+QS+TF-ThM-1 Electronic and Photonic Integrated Devices Enabled by Local III-V on Si Heteroepitaxy**, M. Scherrer, IBM Research GmbH, Zurich Research Laboratory, Switzerland; K. Moselund, Paul Scherrer Institute, Switzerland; **Heinz Schmid**, IBM Research GmbH, Zurich Research Laboratory, Switzerland

Heterogeneous integration of electronic chipllets is one of the key performance drivers in today's HPC and consumer products. Similarly, a performance benefit can be envisioned by heterogeneous integration of preferred materials at the device level. Here we explore this bottom-up path and report on local growth of III-V compound semiconductors on silicon for electronic and photonic applications. For electronic applications the high charge carrier mobility in III-V materials is particularly interesting, while for optical devices, the direct bandgap and in-plane coupling to Si waveguides are key benefits. We will detail the epitaxial growth of III-Vs on Si by template-assisted selective epitaxy using MOCVD and highlight this method's uses by discussing selected device characteristics for field-effect transistors [1] and pin photodetectors directly integrated to Si waveguides [2]. The dense and precise co-placement of III-V gain material with Si allows for novel device designs, which will be illustrated by recent results on lasers based on hybrid III-V/Si photonic crystal cavity designs [3].

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[1] C. Convertino et al. Nat. Electron. (2021) doi.org/10.1038/s41928-020-00531-3

[2] P. Wen et al. Nat. Comm. (2022) doi.org/10.1038/s41467-022-28502-6.

[3] M. Scherrer et al. ACS Photonics (2024) doi.org/10.1021/acsp Photonics.3c01372

8:15am **EM+2D+AP+QS+TF-ThM-2 In situ Graphene Barriers for Remote Epitaxy of SiC**, **Daniel Pennachio**, J. Hajzus, R. Myers-Ward, US Naval Research Laboratory

Remote epitaxy (RE) is a thin film growth technique where epitaxial alignment is directed by interactions with a substrate despite it being covered by a top layer of material.[1] This top layer must be inert and atomically thin for the underlying substrate's potential field to dominate the epitaxial alignment. Since the intermediate layer is inert, the epitaxial thin film is weakly bonded to the substrate and can be removed as a freestanding membrane and the substrate can be reused, without the damage associated with other transfer techniques such as controlled cleaving or ion implantation. Transferred 2D two-dimensional (2D) material, such as graphene, is commonly used for a layer, but the transfer can degrade the film and increase process complexity. To avoid this, we aim to grow in situ graphene in the same chemical vapor deposition (CVD) RE growth as SiC. RE SiC is advantageous since the high cost of SiC makes substrate reuse appealing and isolated SiC membranes are excellent for quantum photonics. Despite these benefits, SiC's high-temperature hydrogen-containing CVD environment can easily damage graphene, making RE difficult.

This study established growth windows for in situ graphene via propane-based hot wall CVD followed by subsequent SiC deposition. Growing at 1620 °C in 20 slm H₂ with 20 sccm propane flow produced predominantly monolayer (ML) graphene films on on-axis 6H-SiC(0001) substrates and 2-3 ML films on 4° off-axis 4H-SiC(0001) substrates with minimal defects found in Raman spectral maps. These films exhibited increased uniformity over graphene grown via Si sublimation from the SiC substrate, as determined by atomic force microscopy (AFM) and Raman spectral maps. This optimal graphene growth condition was used for subsequent RE attempts to study the effect of SiC growth temperature, precursor C/Si ratio, and growth rate on epilayer crystallinity and graphene barrier damage. Nomarski microscopy, scanning electron microscopy (SEM), and AFM found SiC grown at 1620°C with a C/Si ratio of 1.55 to have the smoothest surface morphology and fewest polytype inclusions. SiC crystalline quality appeared correlated to growth rate, with lower growth rates producing smoother films with fewer polytype inclusions. Single-crystalline, polytype-pure SiC epilayers was achieved on 4° off-axis CVD graphene/4H-SiC(0001). Cross-sectional transmission electron microscopy (TEM) of some growth

interfaces in this study exhibited non-uniform multilayer graphitic carbon, motivating further study of this growth system to improve boundary uniformity and SiC epilayer quality.

[1] Kim, Y., Cruz, S., Lee, K. et al. Nature 544, 340–343 (2017).

8:30am **EM+2D+AP+QS+TF-ThM-3 Basal Plane Dislocation Mitigation via Annealing and Growth Interrupts**, **Rachael Myers-Ward**, N. Mahadik, D. Scheiman, J. Hajzus, S. White, D. Pennachio, Naval Research Laboratory

Basal plane dislocations (BPD) in SiC are high-voltage bipolar device killers that source Shockley-type stacking faults in the presence of an electron-hole plasma [1]. Multiple research groups have been successful in mitigating their propagation from the substrate into the epitaxial layer [2-5]. While these are sufficient for typical SiC devices, for high pulsed power current density or high surge current capability applications, the injected carrier concentration is significant enough to expand converted BPDs. Here, we will report results from comparisons of H₂ etching to Ar annealing and the use of H₂ versus Ar during growth interrupts to prevent BPD expansion.

SiC epitaxial layers were grown using a CVD reactor on 4° off-axis substrates toward the [11-20] that are known to have BPDs. A H₂ etch or Ar anneal was performed before the buffer layer (BL) growth while a growth interrupt in H₂ or Ar was conducted prior to the intentionally low doped drift layer. Ultraviolet photoluminescence (UVPL) imaging was used to image the samples before and after UV stressing up to 13 kWcm⁻².

The H₂ etch and H₂ growth interrupt prevented BPDs from expanding under UV stress of 13kWcm⁻² and it is believed that the H₂ treatment specifically inhibited this expansion. To confirm the role of H₂, we performed a growth using the same conditions as the H₂ etch/interrupt, however, an Ar anneal was used instead of a H₂ etch and the growth interrupt was conducted in an Ar atmosphere instead of H₂. The sample was UV stressed up to 1000 Wcm⁻² and it was found that four BPD expanded from the substrate into the epilayer. For comparison, a sample grown with a double H₂ etch (before the buffer layer growth and drift layer) and a sample grown with a H₂ etch plus H₂ growth interrupt did not produce faulting at the same power density. This indicates that H₂ influences BPD expansion. We will present detailed parametric results of samples grown with various etching/annealing, growth interrupts, anneal times, buffer layer thickness, gas flow rates and interrupt temperature, both in H₂ and Ar.

[1]J.P. Bergman, et. al., Mater. Sci. Forum Vol. 353-356, 299 (2001).

[2]N.A. Mahadik et al., Mater Sci Forum 858, 233 (2016).

[3]R. E. Stahlbush, et al., Appl. Phys. Lett. 94, 041916 (2009).

[4]M. Kato, et al., Sci. Rep., 12, 18790 (2022).

[5]N.A. Mahadik et al., Appl. Phys. Lett., 100, 042102 (2012).

8:45am **EM+2D+AP+QS+TF-ThM-4 Shadow Mask Molecular Beam Epitaxy**, S. Mukherjee, R. Sitaram, X. Wang, University of Delaware; **Stephanie Law**, Pennsylvania State University

Shadow mask molecular beam epitaxy (SMMBE) is a form of selective area epitaxy (SAE) which uses a mask either directly fabricated on or placed in contact with the substrate. During film deposition, epitaxial layers are grown on the substrate through apertures in the mask. In addition to selective area growth, SMMBE also produces a shadowing effect near the mask edges in which elemental fluxes vary as a function of position. This results in a gradient of film thickness and/or composition near the mask edges. The steepness of the gradient can be controlled by varying the mask thickness and/or the angle of the mask edges. In this paper, we demonstrate the potential of the SMMBE technique to create in-plane gradient permittivity materials (GPMs) by taking advantage of the shadowing effect. A GPM is a material in which the permittivity varies as a function of location. Our aim is to synthesize in-plane GPMs, in which the permittivity varies in the lateral in-plane direction rather than in the vertical growth direction. In an in-plane GPM, different wavelengths of light can be confined at different in-plane locations on the chip. We are interested in creating an infrared GPM, so we chose Si:InAs as our material. To create our GPMs, we use the SMMBE approach: by creating flux gradients of both indium and silicon near the edges of the mask, we can control the doping density and thus the permittivity of Si:InAs in the lateral in-plane direction. We started with reusable Si masks that are 200 um thick and 1 cm x 1 cm in dimension. Each mask has an aperture at its center which has a dimension of 0.5 cm x 0.5 cm at the top and 0.528 cm x 0.528 cm at the bottom. Nano-FTIR spectra obtained via s-SNOM using a mid-IR nano-FTIR module demonstrates that we successfully synthesized infrared GPMs. The GPM grown using a 200 um mask can confine light with wavenumbers 650 cm⁻¹ to 900 cm⁻¹ over an in-plane distance of 13 um. In this talk, I will discuss the

Thursday Morning, November 7, 2024

influence of several growth parameters in controlling the in-plane permittivity of the GPMs, including the growth temperature, mask thickness, and As:In ratio. In particular, the 500 μm mask provides a larger shadowing effect in comparison to 200 μm mask. This leads to a larger gradient in permittivity over a longer in-plane distance in the GPM: light with wavenumbers 650 cm^{-1} to 1400 cm^{-1} can be confined over an in-plane distance of 30 μm . This provides a larger surface area for the construction of an ultracompact spectrometer. Tailored mask designs can be employed to synthesize in-plane GPMs with tailored permittivity gradients in the future.

9:00am **EM+2D+AP+QS+TF-ThM-5 Impact of Excess Ga on Electronic Properties in Plasma-assisted MBE-grown $\beta\text{-Ga}_2\text{O}_3$.** *Thaddeus Asel, B. Noesges, J. Li, Y. Kim, A. Neal, S. Mou*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA

$\beta\text{-Ga}_2\text{O}_3$ has been of significant interest due to its high electric breakdown field, commercially available native substrate, and shallow n-type donors. However, $\beta\text{-Ga}_2\text{O}_3$ differs from other Ga-based semiconductors where metal-rich growth conditions are utilized to achieve adsorption-controlled growth by consuming the Ga flux entirely. Instead, $\beta\text{-Ga}_2\text{O}_3$ growth must balance the incorporation of Ga with the desorption of a volatile suboxide species, Ga_2O where this suboxide is a limiting step when growing $\beta\text{-Ga}_2\text{O}_3$ via molecular beam epitaxy (MBE) with a traditional Ga source. Increased Ga_2O desorption causes the growth rate of $\beta\text{-Ga}_2\text{O}_3$ to decrease as the Ga flux is increased beyond the stoichiometric point of the material and can impact the stoichiometry of the grown film. In this work, we explore the impact of O-rich and Ga-rich conditions on electronic properties in films of $\beta\text{-Ga}_2\text{O}_3$ grown via plasma-assisted MBE (PAMBE). Initial results comparing two samples under O-rich and Ga-rich conditions showed a large difference in peak low-temperature mobility. The O-rich sample showed a peak low temperature mobility of 793 $\text{cm}^2/\text{V}\cdot\text{s}$ while Ga-rich sample peaked at only 198 $\text{cm}^2/\text{V}\cdot\text{s}$. The mobility and volume carrier density versus temperature data was fit using a model to extract out donor and compensating acceptor density. The Ga-rich sample showed an acceptor concentration of $2.0 \times 10^{16} \text{ cm}^{-3}$ compared to the O-rich sample that was measured to have an acceptor concentration of 3.0×10^{15} , and order of magnitude lower. This is possibly due to the formation of V_{Ga} during the Ga_2O desorption process during the growth of the films. Another series of films were grown across a wider range of O- to Ga-rich conditions to further establish a trend between growth conditions and compensating acceptor density. Only Ga flux varied between samples and substrate temperature, Si source temperature and RF oxygen plasma conditions were held constant. Si concentration in each film was anti-correlated with the growth rate which is expected. Conversely, compensating acceptor density increased with increasing Ga-rich conditions and does not follow the trend of the growth rate. The best peak low-temperature mobility occurred for the sample grown in the most O-rich conditions (789.6 cm^2/Vs) and mobility decreased with increasing compensating acceptor concentration. Overall, these results indicate the importance of Ga:O ratios in $\beta\text{-Ga}_2\text{O}_3$ films grown via MBE with conventional Ga sources. These results demonstrate how improved electronical performance can be achieved in $\beta\text{-Ga}_2\text{O}_3$ by growing under O-rich conditions and limiting the formation of V_{Ga} due to suboxide desorption.

9:15am **EM+2D+AP+QS+TF-ThM-6 Advancing Single-Crystalline Oxide Membrane Growth via Molecular Beam Epitaxy.** *Shivasheesh Varshney, S. Choo*, University of Minnesota; *M. Ramis*, Institute of Materials Science of Barcelona (ICMAB-CSIC), Spain; *L. Thompson, J. Shah, Z. Yang, J. Wen, S. J. Koester, K. Mkhoyan, A. S. McLeod*, University of Minnesota; *M. Coll*, Institute of Materials Science of Barcelona (ICMAB-CSIC), Spain; *B. Jalan*, University of Minnesota

A sacrificial layer method has proven to be an effective route for synthesizing free-standing membranes. In this approach, a crystalline sacrificial layer is selectively dissolved in water, allowing the target film to be transferred onto a host substrate. However, commonly used sacrificial layers (such as $\text{SrCa}_2\text{Al}_2\text{O}_6$) have complex stoichiometry, posing synthesis challenges in molecular beam epitaxy (MBE). In this presentation, we will discuss two distinct but MBE-friendly, fast and facile approaches to synthesize single-crystalline oxide nanomembranes using hybrid MBE [1,2]. In particular, we synthesize epitaxially, single-crystalline SrTiO_3 membranes, ranging from a few unit cells to several hundred nanometers in thickness, using an SrO sacrificial layer, and a solution-processed amorphous $\text{SrCa}_2\text{Al}_2\text{O}_6$ sacrificial layer. Films grows in a layer-by-layer growth mode on a solution-processed amorphous $\text{SrCa}_2\text{Al}_2\text{O}_6$ whereas in a step-flow growth mode on SrO sacrificial layer. Films grown on SrO layer dissolve rapidly (< 5 minutes) in water, resulting in millimeter-sized membranes. Combining

structural characterization using x-ray diffraction (XRD), atomic force microscopy (AFM), piezo force microscopy (PFM), and scanning transmission electron microscopy (STEM), we will present the structure-property relationships in these membranes with particular emphasis on investigating the role of non-stoichiometry on dielectric properties. Using PFM, we demonstrate that Sr-deficient films exhibit robust polarization at room temperature, while stoichiometric films remain consistent with the paraelectric phase. Finally, we will present the growth of single crystalline complex oxide films on a compliant substrate consisting of a few unit-cell SrTiO_3 seed layers onto an amorphous SiO_2 wafer.

1. S. Varshney, S. Choo, L. Thompson, Z. Yang, J. Shah, J. Wen, S. J. Koester, K. A. Mkhoyan, A. McLeod, and B. Jalan, "Hybrid Molecular Beam Epitaxy for Single Crystalline Oxide Membranes with Binary Oxide Sacrificial Layers" *ACS Nano*, **18**, 6348-6358 (2024).
2. S. Varshney, M. Ramis, S. Choo, M. Coll, and B. Jalan, "Epitaxially Grown Single-Crystalline SrTiO_3 Membranes Using a Solution-Processed, Amorphous $\text{SrCa}_2\text{Al}_2\text{O}_6$ Sacrificial Layer" under review (2024) <http://arxiv.org/abs/2405.10464>

Author Index

Bold page numbers indicate presenter

— A —

Asel, Thaddeus: EM+2D+AP+QS+TF-ThM-5, **2**

— C —

Choo, Sooho: EM+2D+AP+QS+TF-ThM-6, **2**

Coll, Mariona: EM+2D+AP+QS+TF-ThM-6, **2**

— H —

Hajzus, Jenifer: EM+2D+AP+QS+TF-ThM-2, **1**;

EM+2D+AP+QS+TF-ThM-3, **1**

— J —

J. Koester, Steven: EM+2D+AP+QS+TF-ThM-6, **2**

Jalan, Bharat: EM+2D+AP+QS+TF-ThM-6, **2**

— K —

Kim, Yunjo: EM+2D+AP+QS+TF-ThM-5, **2**

— L —

Law, Stephanie: EM+2D+AP+QS+TF-ThM-4, **1**

Li, Jian: EM+2D+AP+QS+TF-ThM-5, **2**

— M —

Mahadik, Nadeemullah: EM+2D+AP+QS+TF-ThM-3, **1**

Mkhoyan, K. Andre: EM+2D+AP+QS+TF-ThM-6, **2**

Moselund, Kirsten E.: EM+2D+AP+QS+TF-ThM-1, **1**

Mou, Shin: EM+2D+AP+QS+TF-ThM-5, **2**

Mukherjee, Shagorika: EM+2D+AP+QS+TF-ThM-4, **1**

Myers-Ward, Rachael: EM+2D+AP+QS+TF-ThM-2, **1**; EM+2D+AP+QS+TF-ThM-3, **1**

— N —

Neal, Adam: EM+2D+AP+QS+TF-ThM-5, **2**

Noesges, Brenton: EM+2D+AP+QS+TF-ThM-5, **2**

— P —

Pennachio, Daniel: EM+2D+AP+QS+TF-ThM-2, **1**; EM+2D+AP+QS+TF-ThM-3, **1**

— R —

Ramis, Martí: EM+2D+AP+QS+TF-ThM-6, **2**

— S —

S. McLeod, Alexander: EM+2D+AP+QS+TF-ThM-6, **2**

Scheiman, David: EM+2D+AP+QS+TF-ThM-3, **1**

Scherrer, Markus: EM+2D+AP+QS+TF-ThM-1, **1**

Schmid, Heinz: EM+2D+AP+QS+TF-ThM-1, **1**

Shah, Jay: EM+2D+AP+QS+TF-ThM-6, **2**

Sitaram, Rahul: EM+2D+AP+QS+TF-ThM-4, **1**

— T —

Thompson, Liam: EM+2D+AP+QS+TF-ThM-6, **2**

— V —

Varshney, Shivasheesh: EM+2D+AP+QS+TF-ThM-6, **2**

— W —

Wang, Xi: EM+2D+AP+QS+TF-ThM-4, **1**

Wen, Jiakuan: EM+2D+AP+QS+TF-ThM-6, **2**

White, Samuel: EM+2D+AP+QS+TF-ThM-3, **1**

— Y —

Yang, Zhifei: EM+2D+AP+QS+TF-ThM-6, **2**